

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	749	257/735	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 14:06
L2	367	257/736	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 14:06
L3	3514	257/737	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 14:33
L4	2559	257/706	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 14:59
L5	2013	257/707	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 15:25
L6	264	257/711	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 15:42
L7	316	257/276	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 15:59
L8	2160	257/780	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 16:12

L9	1131	257/781	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 16:47
L10	1677	257/783	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 16:57
L11	562	257/772	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 17:13
L12	3211	257/787	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 17:18
L13	1883	257/713	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 17:49
L14	1030	257/775	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 18:06
L17	1357	257/341	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 18:20
L18	990	257/796	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 18:34

L19	2387	257/690	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 18:34
S1	3	power near MOSFET and die near (pad or plate or paddle) with gate same source and heat	USPAT	OR	OFF	2005/04/13 22:29
S2	10	MOSFET and die near (pad or plate or paddle) with gate same source and heat	USPAT	OR	OFF	2005/04/12 18:18
S3	361	MOSFET and (pad or plate or paddle) with gate same source and heat	USPAT	OR	OFF	2005/04/12 19:55
S4	13	MOSFET and (pad or plate or paddle) with gate same source and heat	USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 19:59
S5	228	MOSFET with gate same source and heat	USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 20:11
S6	12	MOSFET and (lead) with gate same source and heat	USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 20:12
S7	242	MOSFET and (lead) with gate same source and heat	USPAT	OR	OFF	2005/04/12 20:12
S8	712	257/735	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 22:16
S9	348	257/736	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/13 14:40
S10	8	"6566164"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/13 14:40
S11	2957	257/737	USPAT	OR	OFF	2005/04/13 16:52

S12	3334	257/737	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/13 16:53
S13	2416	257/706	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/13 17:49
S14	1937	257/707	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/13 16:55
S15	127	257/707 and die near (pad or pallet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/13 16:54
S16	1114	(semiconductor or die or chip or IC) and heat and die near (pad or pallet) and (encapsulat\$3 or mold\$3)	USPAT	OR	OFF	2005/04/13 17:12
S17	286	(semiconductor or die or chip or IC) and heat with (lid or cap or heat near sink) and die near (pad or pallet) and (encapsulat\$3 or mold\$3)	USPAT	OR	OFF	2005/04/13 17:45
S18	418	(semiconductor or die or chip or IC) and (lid or cap or heat near sink) and die near (pad or pallet) and (encapsulat\$3 or mold\$3)	USPAT	OR	OFF	2005/04/13 17:46
S19	212	(semiconductor or die or chip or IC) and (lid or cap or heat near sink) and die near (pad or pallet) and (encapsulat\$3 or mold\$3) and (ball or bump)	USPAT	OR	OFF	2005/04/13 18:49
S20	748	(semiconductor or die or chip or IC) and (lid or cap or heat near sink) and lead near frame and (encapsulat\$3 or mold\$3) and (ball or bump)	USPAT	OR	OFF	2005/04/13 19:08
S21	2799	(semiconductor or die or chip or IC) and (lid or cap or heat near sink) and lead and (encapsulat\$3 or mold\$3) and (ball or bump)	USPAT	OR	OFF	2005/04/13 19:08

S22	2051	S21 not S20	USPAT	OR	OFF	2005/04/13 19:08
S23	29	(semiconductor or die or chip or IC) and (lid or cap or heat near sink) with bent and lead and (encapsulat\$3 or mold\$3) and (ball or bump)	USPAT	OR	OFF	2005/04/13 19:09
S24	656	(semiconductor or die or chip or IC) and (lid or cap or heat near sink) with cover\$3 and lead and (encapsulat\$3 or mold\$3) and (ball or bump)	USPAT	OR	OFF	2005/04/13 19:22
S25	48	(semiconductor or die or chip or IC) and (lid or cap or heat near sink) with (paddle or foot) and lead and (encapsulat\$3 or mold\$3) and (ball or bump)	USPAT	OR	OFF	2005/04/13 19:14
S26	68	(semiconductor or die or chip or IC) and (lid or cap or heat near sink) with (paddle or foot) and (encapsulat\$3 or mold\$3) and (ball or bump)	USPAT	OR	OFF	2005/04/13 19:14
S27	283	(semiconductor or die or chip or IC) and (lid or cap or heat near sink) with cover\$3 and die with (pad or mount\$3 or paddle or pellet) and (encapsulat\$3 or mold\$3) and (ball or bump)	USPAT	OR	OFF	2005/04/13 19:33
S28	31	257/676 and (lid or cap or heat near sink) with cover\$3 and die with (pad or mount\$3 or paddle or pellet) and (encapsulat\$3 or mold\$3) and (ball or bump)	USPAT	OR	OFF	2005/04/13 19:32
S29	50	257/676 and (lid or cap or heat near sink) with cover\$3 and (encapsulat\$3 or mold\$3) and (ball or bump)	USPAT	OR	OFF	2005/04/13 19:32
S30	709	(semiconductor or die or chip or IC) and (lid or cap or heat near sink) with cover\$3 and die with (pad or mount\$3 or paddle or pellet) and (encapsulat\$3 or mold\$3)	USPAT	OR	OFF	2005/04/14 02:06
S31	426	S30 not S27	USPAT	OR	OFF	2005/04/13 19:33
S32	1938	(semiconductor or die or chip or IC) and (lid or cap or heat near sink) with expos\$3 and (encapsulat\$3 or mold\$3)	USPAT	OR	OFF	2005/04/13 19:46
S33	47	power near MOSFET and pad with (aluminum or "Al") and heat	USPAT	OR	ON	2005/04/13 23:28

S34	485522	power near MOSFET and pad with (aluminum or "Al") and heat and (thickness or height) of adhesive	USPAT	OR	ON	2005/04/13 22:31
S35	0	power near MOSFET and pad with (aluminum or "Al") and heat and (thickness or height) with adhesive	USPAT	OR	ON	2005/04/14 00:23
S36	0	power near MOSFET and pad with (gold or "Au") with (ball or bump) same (ball or bump) with adhesive and adhesive with (silver or "Ag") near paste	USPAT	OR	ON	2005/04/13 23:29
S37	0	power near MOSFET and pad with (gold or "Au") with (ball or bump) and (ball or bump) with (adhesive or underfill) and (adhesive or underfill) with (silver or "Ag") near paste	USPAT	OR	ON	2005/04/13 23:30
S38	4	(semiconductor or die or chip or IC) and pad with (gold or "Au") near wire with (ball or bump) and (ball or bump) with (adhesive or underfill) and (adhesive or underfill) with (silver or "Ag") near paste	USPAT	OR	ON	2005/04/13 23:30
S39	13	power near MOSFET and (adhesive or glue) with thickness	USPAT	OR	ON	2005/04/14 01:28
S40	255	257/711	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 01:39
S41	304	257/276	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 01:40
S42	3032	257/787	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 01:54
S43	79	257/787 and mosfet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 01:41

S44	539	257/772	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 02:09
S45	419	(semiconductor or die or chip or IC) and (lid or cap or heat) with cover\$3 and die with (pad or mount\$3 or paddle or pellet) and (encapsulat\$3 or mold\$3) and (ball or bump)	USPAT	OR	OFF	2005/04/14 02:20
S46	1609	257/783	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 02:19
S47	1074	257/781	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 02:33
S48	1174	(semiconductor or die or chip or IC) and (lid or cap or heat) with cover\$3 and die with (pad or mount\$3 or paddle or pellet) and (encapsulat\$3 or mold\$3)	USPAT	OR	OFF	2005/04/14 02:38
S49	755	S48 not S45	USPAT	OR	OFF	2005/04/14 02:21
S50	2050	257/780	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 03:10
S51	135	(semiconductor or die or chip or IC) and (lid or cap or heat) with cover\$3 and die with (pad or mount\$3 or paddle or pellet) with expos\$3 and (encapsulat\$3 or mold\$3)	USPAT	OR	OFF	2005/04/14 03:47
S52	1	"6552428".PN.	USPAT; USOCR	OR	OFF	2005/04/14 02:39
S53	1	"4935803".PN.	USPAT; USOCR	OR	OFF	2005/04/14 02:53
S54	1	"5532512".PN.	USPAT; USOCR	OR	OFF	2005/04/14 02:53
S55	1	"5814884".PN.	USPAT; USOCR	OR	OFF	2005/04/14 02:53

S56	1	"6040626".PN.	USPAT; USOCR	OR	OFF	2005/04/14 02:54
S57	1	"6077727".PN.	USPAT; USOCR	OR	OFF	2005/04/14 02:54
S58	1	"6084310".PN.	USPAT; USOCR	OR	OFF	2005/04/14 02:54
S59	1	"6249041".PN.	USPAT; USOCR	OR	OFF	2005/04/14 02:55
S60	1	"6423623".PN.	USPAT; USOCR	OR	OFF	2005/04/14 02:55
S61	80163	mosfet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 02:56
S62	31907	mosfet and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 02:56
S63	1059	mosfet and electrode near plate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 02:57
S64	755	mosfet and electrode near plate	USPAT; JPO	OR	ON	2005/04/14 03:05
S65	50	mosfet and electrode near plate with exposed	USPAT; JPO	OR	ON	2005/04/14 03:05
S66	21	mosfet and (lid or cap or heat) with cover\$3 and (pad or mount\$3 or paddle or pellet) with expos\$3 and (encapsulat\$3 or mold\$3)	USPAT	OR	OFF	2005/04/14 03:09
S67	27	mosfet and (lid or cap or heat) with cover\$3 and (gate or source) with expos\$3 and (encapsulat\$3 or mold\$3)	USPAT	OR	OFF	2005/04/14 03:10
S68	1805	257/713	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 03:36

S69	980	257/775	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 03:51
S70	0	(semiconductor or die or chip or IC) and (lid or cap or heat) with cover\$3 and die with (pad or mount\$3 or paddle or pellet) with expos\$3 and (encapsulat\$3 or mold\$3)	JPO	OR	OFF	2005/04/14 03:48
S71	17	(semiconductor or die or chip or IC) and (lid or cap or heat) and die with (pad or mount\$3 or paddle or pellet) with expos\$3 and (encapsulat\$3 or mold\$3)	JPO	OR	OFF	2005/04/14 03:49
S72	115	(semiconductor or die or chip or IC) and (lid or cap or heat) and (pad or mount\$3 or paddle or pellet) with expos\$3 and (encapsulat\$3 or mold\$3)	JPO	OR	OFF	2005/04/14 03:49
S73	4322	(semiconductor or die or chip or IC) and (lid or cap or heat) and (pad or mount\$3 or paddle or pellet) with expos\$3 and (encapsulat\$3 or mold\$3)	USPAT	OR	OFF	2005/04/14 03:49
S74	1463	(semiconductor or die or chip or IC) and (lid or cap or heat) with expos\$3 and (pad or mount\$3 or paddle or pellet) with expos\$3 and (encapsulat\$3 or mold\$3)	USPAT	OR	OFF	2005/04/14 03:50
S75	1288	257/341	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 05:20
S76	952	257/796	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 05:20